80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX T_C = +25°C
80V	25mΩ @ V_{GS} = 10V	27A
	41mΩ @ V_{GS} = 4.5V	21A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

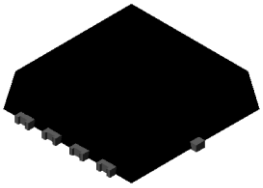
Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Small Form Factor, Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

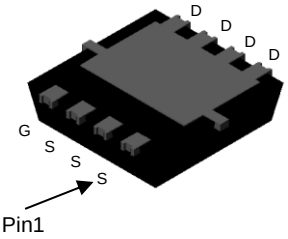
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

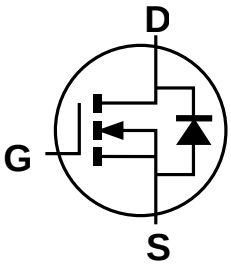
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



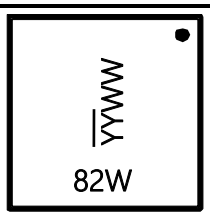
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8028LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape and Reel
DMTH8028LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape and Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



82W = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = 10V	T_C = +25°C	I_D	27	A
	T_C = +100°C		19	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	108	A
Maximum Continuous Body Diode Forward Current (Note 7)		I_S	27	A
Pulsed Body Diode Forward Current		I_{SM}	108	A
Avalanche Current, L = 0.3mH (Note 8)		I_{AS}	12.5	A
Avalanche Energy, L = 0.3mH (Note 8)		E_{AS}	23.4	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 6)		P_D	3.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	4.0	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	80	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 64V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.3	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	17	25	mΩ	V_{GS} = 10V, I_D = 5A
		—	26	41		V_{GS} = 4.5V, I_D = 4.5A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 5A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	631	—	pF	V_{DS} = 40V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	200	—		
Reverse Transfer Capacitance	C_{rss}	—	19.5	—		
Gate Resistance	R_g	—	1.1	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	5.4	—	nC	V_{DS} = 40V, I_D = 7.5A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	10.4	—		
Gate-Source Charge	Q_{gs}	—	1.8	—		
Gate-Drain Charge	Q_{gd}	—	2.4	—		
Turn-On Delay Time	$t_{D(ON)}$	—	7.1	—	ns	V_{DD} = 40V, V_{GS} = 4.5V, R_G = 2.7Ω, I_D = 10A
Turn-On Rise Time	t_R	—	9.7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	18.6	—		
Turn-Off Fall Time	t_F	—	8.6	—		
Body Diode Reverse Recovery Time	t_{RR}	—	28.5	—	ns	I_F = 7.5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	21.7	—	nC	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

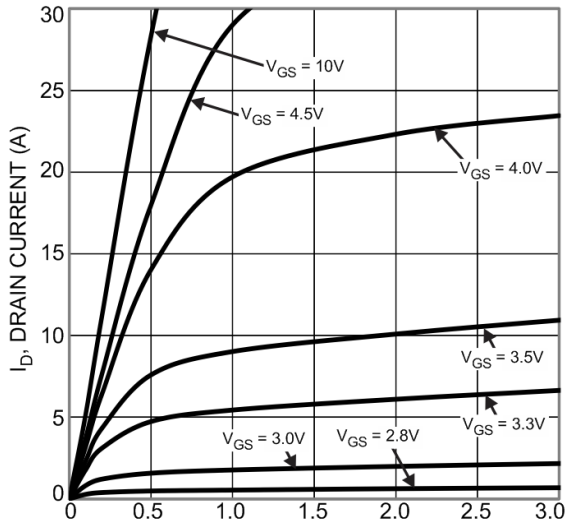


Fig. 1 Typical Output Characteristic

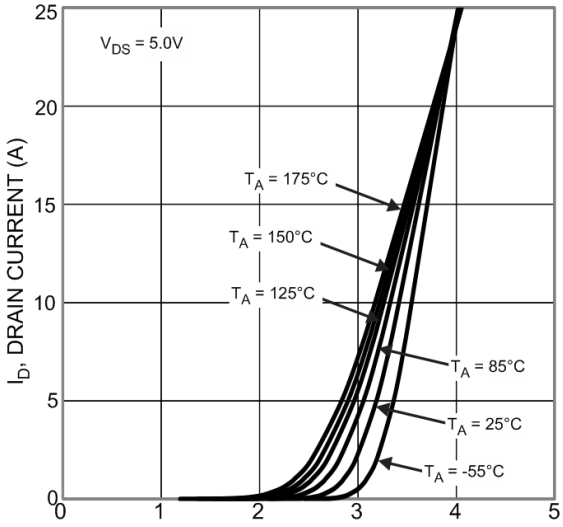


Fig. 2 Typical Transfer Characteristics

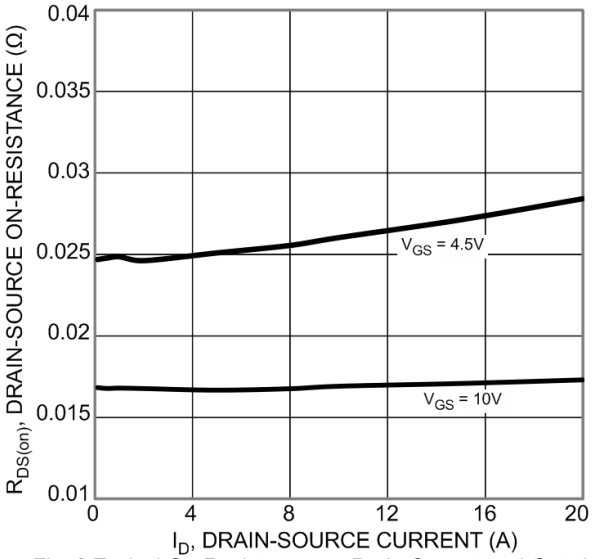


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

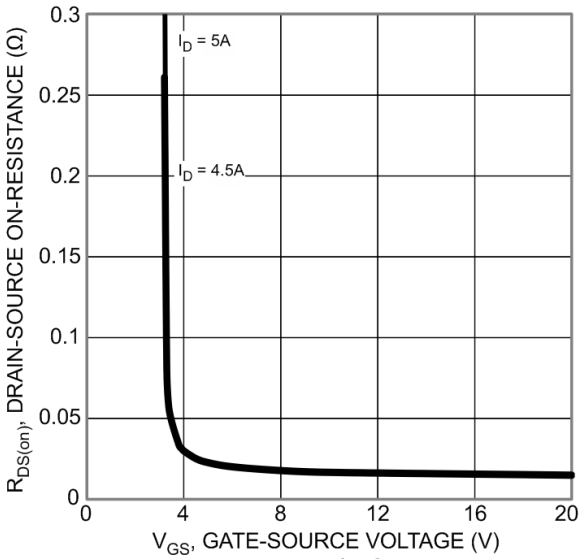


Fig. 4 Typical Transfer Characteristic

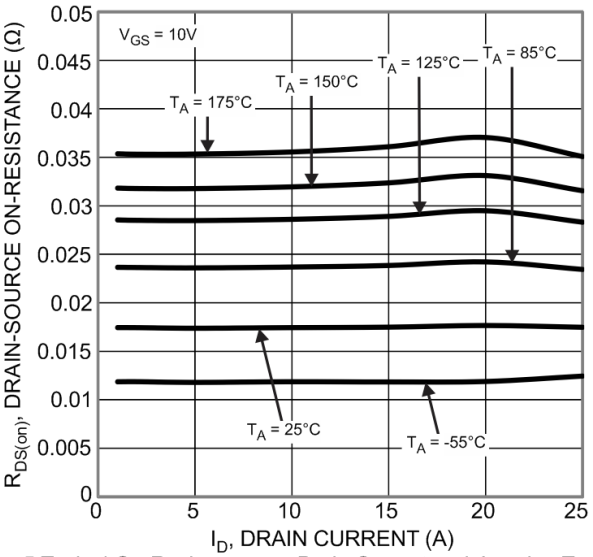


Fig. 5 Typical On-Resistance vs. Drain Current and Junction Temperature

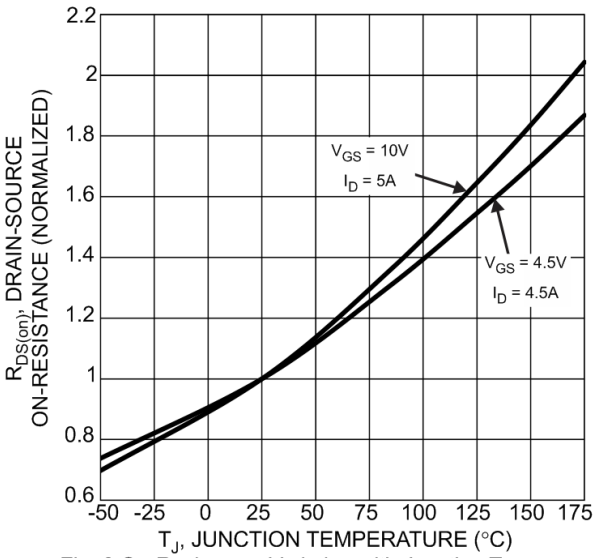


Fig. 6 On-Resistance Variation with Junction Temperature

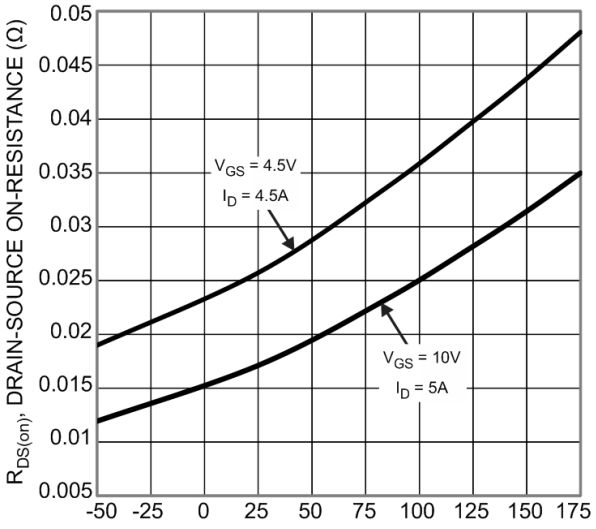


Fig. 7 On-Resistance Variation with Junction Temperature

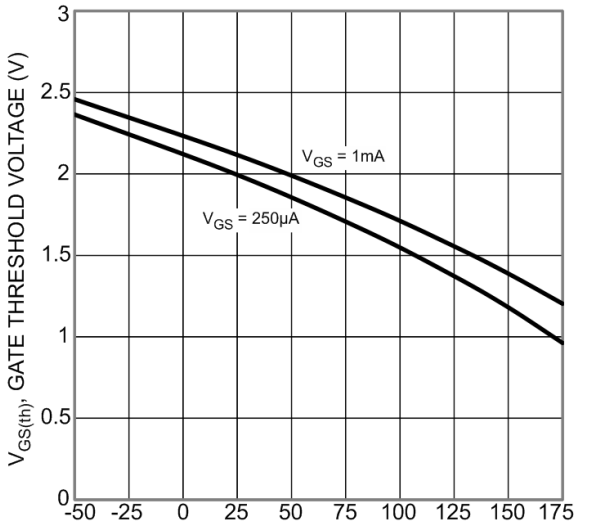


Fig. 8 Gate Threshold Variation vs Junction Temperature

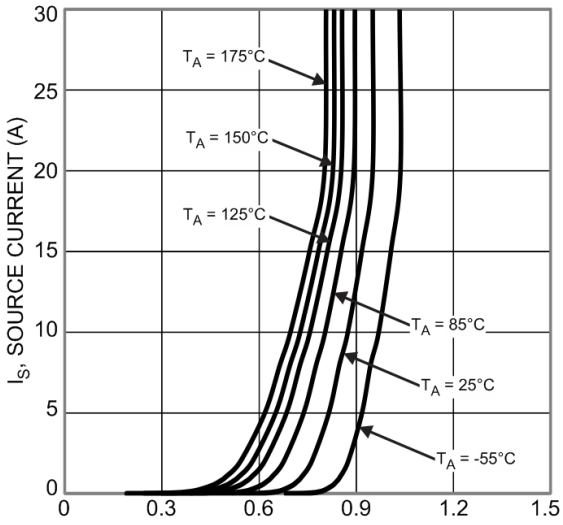


Fig. 9 Diode Forward Voltage vs Current

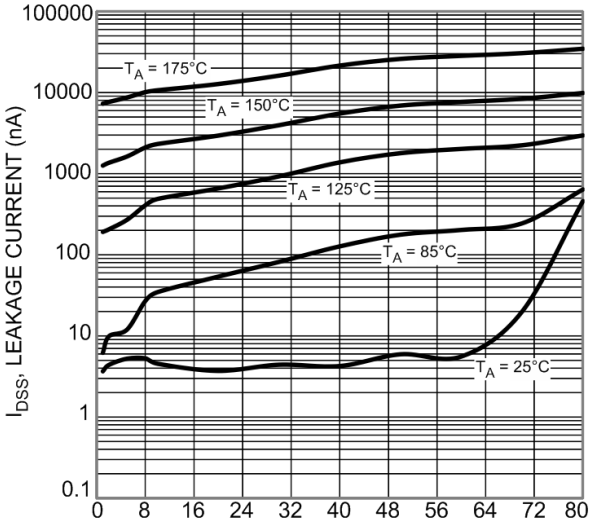


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

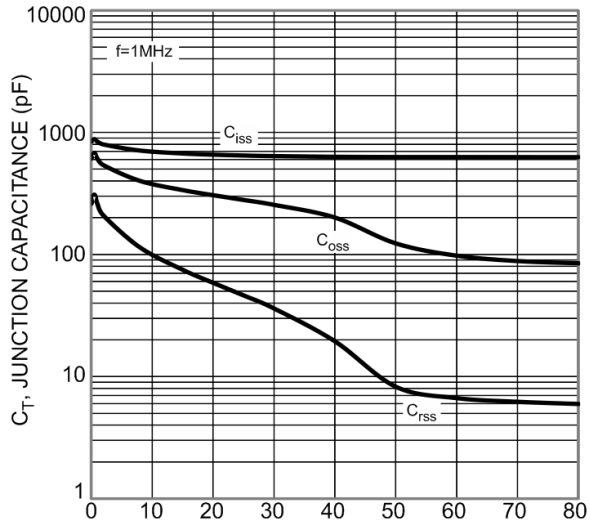


Fig. 11 Typical Junction Capacitance

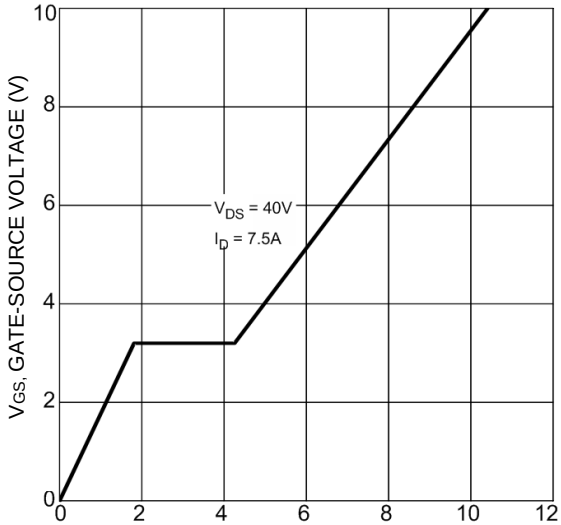


Fig. 12 Gate Charge

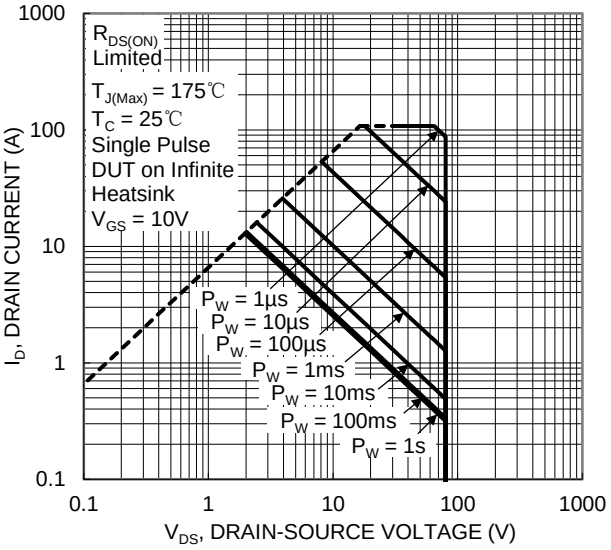


Fig. 13 SOA, Safe Operation Area

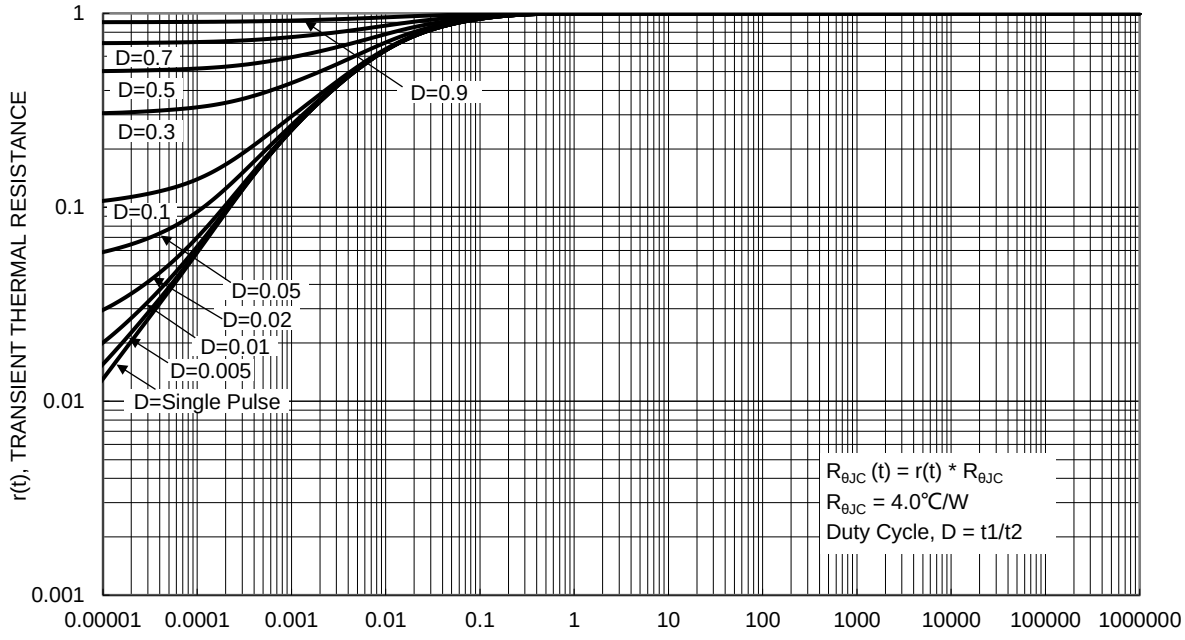
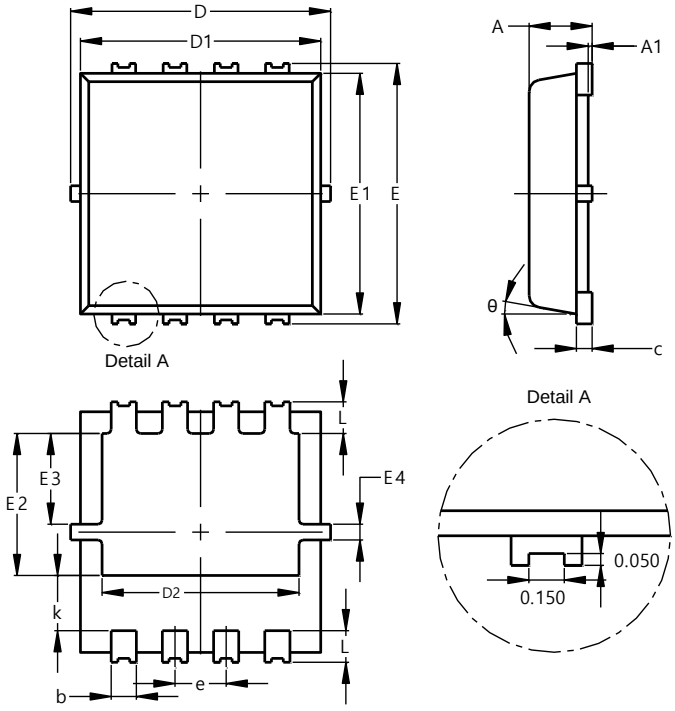


Fig. 14 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

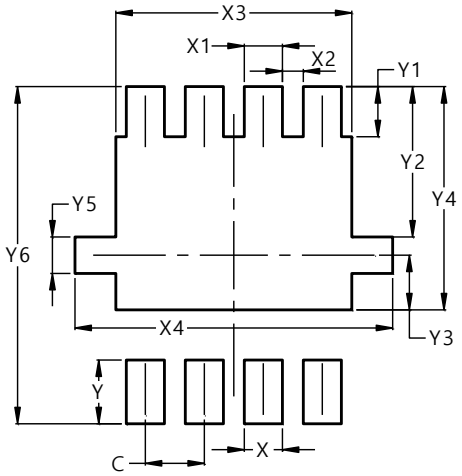


PowerDI3333-8 (SWP) (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	–	–	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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